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Altri autori (Persone)	IraceAndrea BreglioGiovanni
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Nota di contenuto	Intro -- Growing and Forming of Semiconductor Layers -- Preface -- Table of Contents -- Polarity Effect on the Heteroepitaxial Growth of BxC on 4H-SiC by CVD -- Vertical Current Transport in Monolayer MoS2 Heterojunctions with 4H-SiC Fabricated by Sulfurization of Ultra-Thin MoOx Films -- Estimation of Influence on Carbon Vacancy Regarding 4H-SiC Substrate Grown by HTCVD Method -- Resistivity as a Witness of Local Crystal Growth Conditions -- GaN Cap UV Spectroscopy Assessment in AlGaN/GaN HEMT -- SNDM Study of the MOS Interface State Densities on the 3C-SiC / 4H-SiC Stacked Structure -- Development of 200mm SiC Technology - Epitaxial Thickness Uniformity Observation on Different 8 Inch 4H-SiC Substrates -- 4H-SiC Crystal Growth Using Recycled SiC Powder Source -- High-Quality SiC Crystal Growth by Temperature Gradient Control at Initial Growth Stage -- The Role of Air-Pocket in Crucible Structure for High Quality SiC Crystal Growth -- Influence of the Size Distribution of the SiC Powder Source on the Shape of the Crystal Growth Interface during PVT Growth of 4H-SiC Boules -- Confirmation of the Growth Mechanism of the Buffer Layer in Epitaxial Graphene on SiC -- Suppressing the Memory Effect in Al Doped 3C-SiC Grown Using Chlorinated Chemistry -- Investigations into the Impact of Deposition or Growth Techniques

on the Field Oxide TID Response for 4H-SiC Space Applications --
Characterization of Growth Sectors in Gallium Nitride Substrate Wafers
-- Doping Efficiency and Long-Term Stability of Various SiC Epitaxial
Reactors and Process Chemistries -- Keyword Index -- Author Index.

Sommario/riassunto

Special topic volume with invited peer-reviewed papers only.

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The first in a triennial series of international conferences on the
property and application of dielectric materials, this conference is now
a major event on the international conference circuit.